L Number	Hits	Search Text	DB	Time stamp
1	8	(("6114230") or ("6074939") or	TICDAM.	2004/05/05
	8	(("6114230") or ("6074939") or ("6037228") or ("6001541") or ("5759916") or ("5733712") or ("5554486") or	USPAT; US-PGPUB	2004/05/05
		("5545588")).PN.		
2	4	((("6114230") or ("6074939") or	USPAT;	2004/05/05
	_	("6037228") or ("6001541") or ("5759916")	US-PGPUB	10:27
		or ("5733712") or ("5554486") or		== -
		("5545588")).PN.) and ARC		
3	3	(((("6114230") or ("6074939") or	USPAT;	2004/05/05
		("6037228") or ("6001541") or ("5759916")	US-PGPUB	10:27
		or ("5733712") or ("5554486") or	00 10102	20.27
		("5545588")).PN.) and ARC) and plasma		
4	192	ARC with SiON	USPAT;	2004/05/05
-			US-PGPUB	10:30
5	l 0	(ARC with SiON) same (resistance with	USPAT;	2004/05/05
-	_	(oxygen or "0.sub.2"))	US-PGPUB	10:31
6	33	(ARC with SiON) same ((oxygen or	USPAT;	2004/05/05
-		"O.sub.2"))	US-PGPUB	10:31
7	31	((ARC with SiON) same ((oxygen or	USPAT;	2004/05/05
'	,	"O.sub.2"))) and @ad<20020219	US-PGPUB	10:38
8	11	(((ARC with SiON) same ((oxygen or	USPAT;	2004/05/05
		"O.sub.2"))) and @ad<20020219) and (low	US-PGPUB	10:36
		with (k or dielectric))		• • •
9	1	(ARC with SiON) same (resistance or	USPAT;	2004/05/05
		resistant) same (oxygen or "O.sub.2")	US-PGPUB	10:38
10	18	(ARC with SiON) and ((resistance or	USPAT;	2004/05/05
		resistant) same (oxygen or "O.sub.2"))	US-PGPUB	10:43
11	15	((ARC with SiON) and ((resistance or	USPAT;	2004/05/05
		resistant) same (oxygen or "O.sub.2")))	US-PGPUB	10:43
		and @ad<20020219		
12	0	(ARC with SiON) and ((resistance or	EPO; JPO;	2004/05/05
		resistant) same (oxygen or "O.sub.2"))	DERWENT;	10:43
		,, ,, ,, ,, ,, ,, ,, ,, ,, ,, ,, ,, ,,	IBM TDB	
13	0	(ARC with SiON) and (resist same (oxygen	EPO; JPO;	2004/05/05
		or "0.sub.2"))	DERWENT;	10:43
			IBM TDB	
14	31	(ARC with SiON) and (resist same (oxygen	USPAT;	2004/05/05
		or "0.sub.2"))	US-PGPUB	10:43
15	26	((ARC with SiON) and (resist same (oxygen	USPAT;	2004/05/05
		or "0.sub.2"))) and @ad<20020219	US-PGPUB	11:48
16	1382	ARC and (low with (k or dielectric)) and	USPAT;	2004/05/05
		(resist or mask or photoresist)	US-PGPUB	11:48
17	3	(ARC and (low with (k or dielectric)) and	USPAT;	2004/05/05
		(resist or mask or photoresist)) and	US-PGPUB	11:58
		(polymer with (wet near3 etching))		
18	3	((ARC and (low with (k or dielectric)) and	USPAT;	2004/05/05
		(resist or mask or photoresist)) and	US-PGPUB	11:49
		(polymer with (wet near3 etching))) and		
		@ad<20020219		
19	5	(ARC and (low with (k or dielectric)) and	USPAT;	2004/05/05
		(resist or mask or photoresist)) and	US-PGPUB	11:49
		((organic or residue) with (wet near3		
		etching))		
20	5	((= = = = = , ,)	USPAT;	2004/05/05
		(resist or mask or photoresist)) and	US-PGPUB	11:58
		((organic or residue) with (wet near3		
	_	etching))) and @ad<20020219		
21	12	(ARC and (low with (k or dielectric)) and	USPAT;	2004/05/05
		(resist or mask or photoresist)) and	US-PGPUB	11:58
	_	(cleaning with (wet near3 etching))		
22	8	((ARC and (low with (k or dielectric)) and	USPAT;	2004/05/05
		(resist or mask or photoresist)) and	US-PGPUB	12:47
		(cleaning with (wet near3 etching))) and		
, ,	627477	@ad<20020219		0004/05/05
23	627471	(organic or (low adj (K or dielectric)))	USPAT;	2004/05/05
124	2401	(love and the amendal actual assume the second	US-PGPUB	12:45
24	3491	(low adj (K or dielectric)) same (trench	USPAT;	2004/05/05
		or via or opening or hole or aperture or	US-PGPUB	12:46
L		recess)	L	

25	299	((low adj (K or dielectric)) same (trench	USPAT;	2004/05/05
		or via or opening or hole or aperture or	US-PGPUB	12:46
		recess)) and arc		
26	231		USPAT;	2004/05/05
		(trench or via or opening or hole or	US-PGPUB	12:47
		aperture or recess)) and arc) and (resist		
1		or photoresist or photomask)		, , ,
27	89	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/05/05
		(trench or via or opening or hole or	US-PGPUB	12:47
	1	aperture or recess)) and arc) and (resist		
		or photoresist or photomask)) and		
		(precleaning or cleaning or clean or		
		preclean)	IICDAM.	2004/05/05
28	55	(((((low adj (K or dielectric)) same	USPAT; US-PGPUB	12:54
		(trench or via or opening or hole or aperture or recess)) and arc) and (resist	03-PGP0B	12:54
		or photoresist or photomask)) and		
		(precleaning or cleaning or clean or		
		preclean)) and @ad<20020219		
29	23	•	USPAT;	2004/05/05
2 3	23	(trench or via or opening or hole or	US-PGPUB	12:54
		aperture or recess)) and arc) and (resist		
		or photoresist or photomask)) and	ĺ	
		(precleaning or cleaning or clean or		
		preclean)) and @ad<20020219) and wet		